

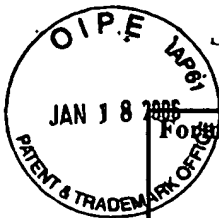


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| Form 1449 (Modified) | Atty Docket No. NOVLP090/NVLS-2888 | Application No.: 10/733,858 |
| Information Disclosure Statement By Applicant | Applicant: Zhu et al. | |
| (Use Several Sheets if Necessary) | Filing Date December 10, 2003 | Group 2891 |

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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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Foreign Patent or Published Foreign Patent Application

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation | |
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

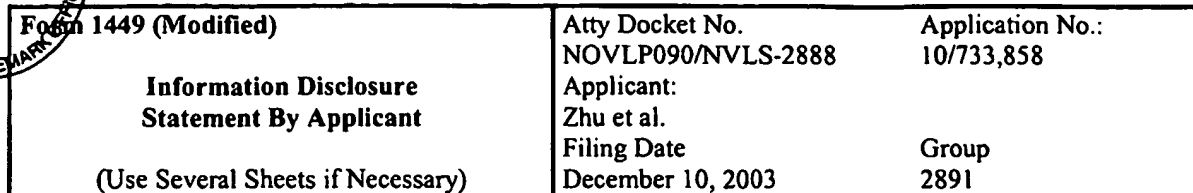


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